

BTA08

双向可控硅
TRIAC

版本号
201603-A

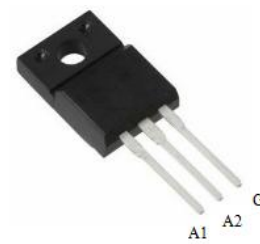
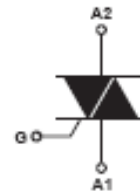
产品概述 GENERAL DESCRIPTION

BTA08 双向可控硅采用穿通隔离台面结构,复合玻璃钝化PN结表面保护工艺技术, dv/dt高,可靠性高,适用于控温、调光、马达控制。

BTA08 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT(III)}$	≤ 50	mA
V_{ISO}	2000	V



TO-220F

产品特性

FEATURES

- dv/dt高
- 通态压降低
- Rohs环保产品
- Highly dv/dt
- Low on-state voltage
- Rohs Products

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

极限值(除非另有规定, T_j=25℃) ABSOLUTE RATINGS

(T_j=25℃, unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
I _{T(RMS)}	RMS 通态电流 RMS on-state current (full sine wave)	T _C =110℃	8 A
I _{TSM}	通态峰值浪涌电流 Non repetitive surge peak on-state current	F=50Hz, t=20ms	80 A
I ² t	I ² t 耗散值 I ² t value for fusing	T _p =10ms	36 A ² s
di/dt	通态电流上升值 Critical rate of rise of on-state current	F=120Hz, T _j =125℃	50 A/μs
I _{GM}	门极峰值电流 Peak gate current	T _p =20μs, T _j =125℃	4 A
P _{G(AV)}	平均门极耗散功率 Average gate power dissipation	T _j =125℃	1 W
T _{stg}	贮存结温范围 Storage junction temperature range		-40~+150 ℃
T _j	工作结温范围 Operating junction temperature range		-40~+150 ℃

电参数(除非另有规定, T_j=25℃) ELECTRICAL CHARACTERISTICS

(T_j=25℃, unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value			单位 Unit	测试条件 Test Conditions	
		Min.	Typ.	Max.			
触发电流 Gate trigger current	I _{GT}	I ~ III	10	-	35	mA	V _D =12V, I _T =0.1A
触发电压 Gate trigger voltage	V _{GT}	I ~ III	≤1.5			V	V _D =12V, I _T =0.1A
维持电流 Holding current	I _H		-	-	50	mA	V _D =12V, I _T =0.1A
擎住电流 Latching current	I _L		-	-	80	mA	V _D =12V, I _T =0.1A
电压上升率 Rise of off- state voltage	dv/dt		1000	-	-	V/μS	V _D =67% V _{DRM}
通态压降 Peak on-state voltage	V _{TM}		≤1.55			V	I _T =11A
断态漏电流 Peak repetitive forward blocking current	I _{DRM}		≤5			μA	V _{RRM} =V _{DRM} , T _j = 25 ℃
	I _{RRM}		≤3.1			mA	V _{RRM} =V _{DRM} , T _j = 150 ℃

热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
R _{th(j-c)}	Junction to case(AC)	1.7	K/W
R _{th(j-a)}	Junction to ambient	60	K/W

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系
Fig.1.Maximum Power Dissipation Versus on-state current

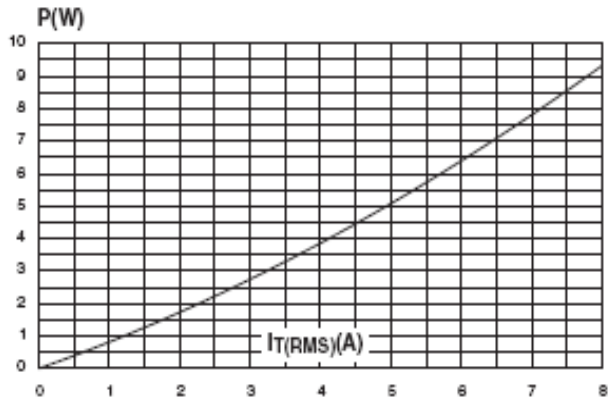


图3 通态特性
Fig.3.On-State Characteristics

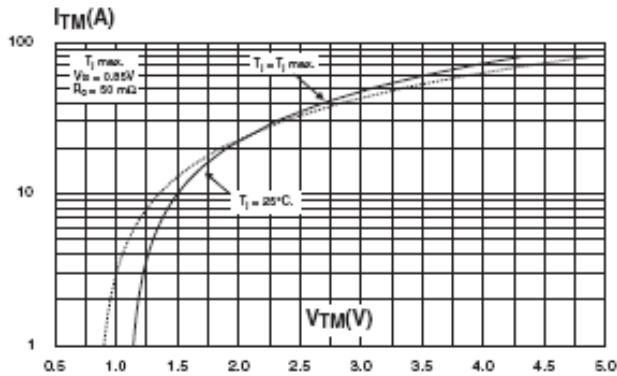


图5 I_{GT} 、 I_H 、 I_L 相对值（相对于25°C）与结温关系

Fig.5.Relative Variation Of Gate Trigger Current , Holding Current And Latching Current Versus Junction Temperature (Typical Value)

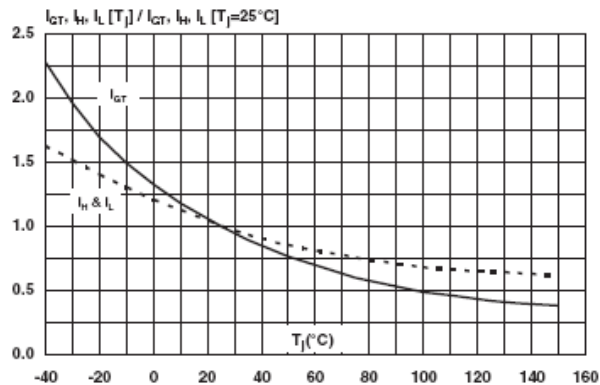


图2 RMS通态电流与Tc温度关系
Fig.2. RMS On-state Current Versus TL

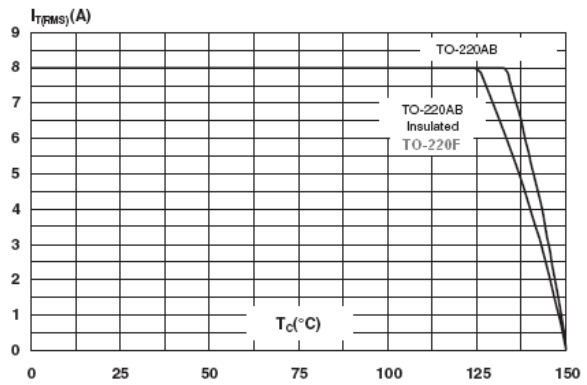
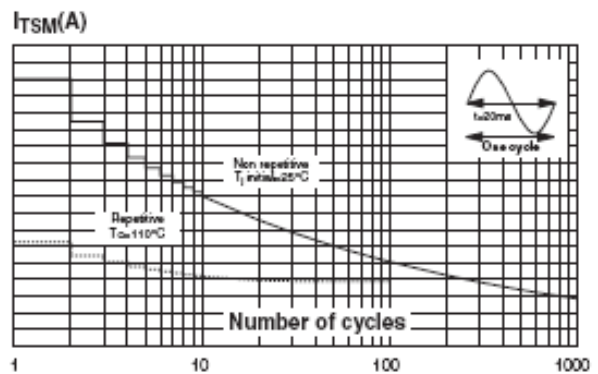
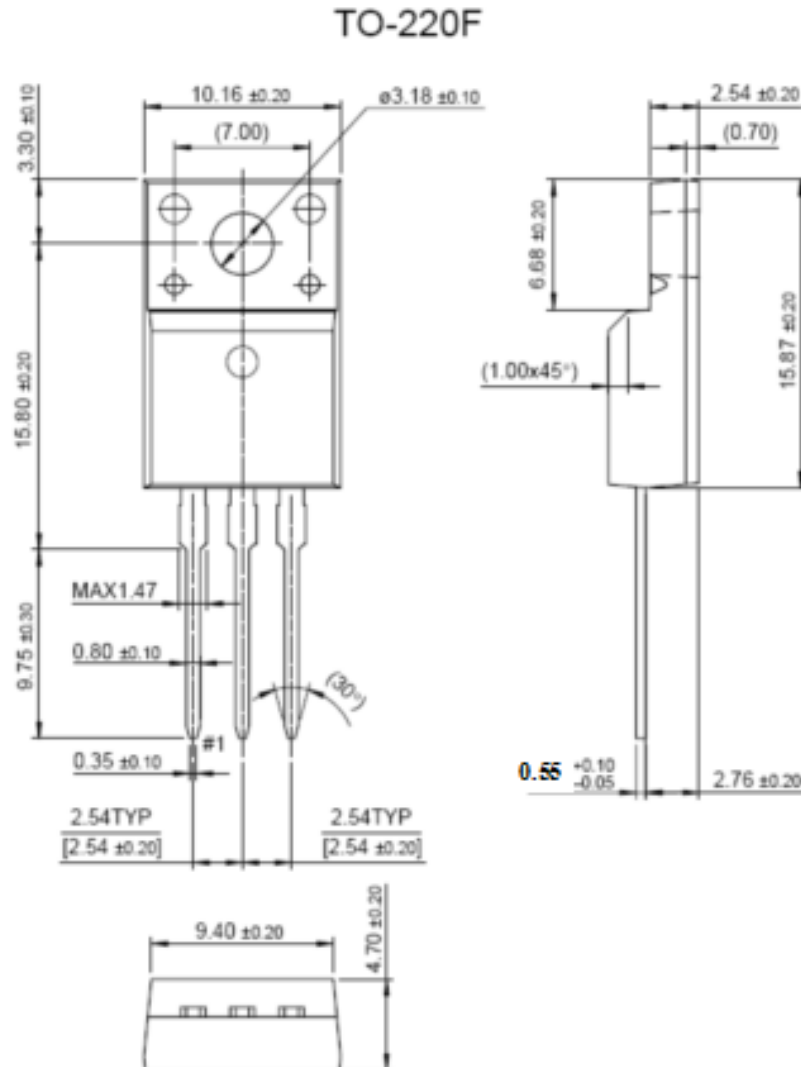


图4 通态浪涌峰值电流与周期数关系
Fig.4.Surge Peak On-state Current Versus Number Cycles



封装尺寸 PACKAGE MECHANICAL DATA



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